

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI OSC-0.7L** is Designed for

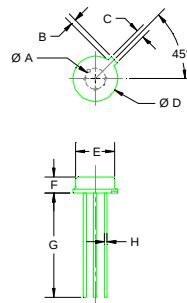
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	500 mA
V_{CB}	40 V
P_{DISS}	7.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	25°C/W

PACKAGE STYLE TO-46



DIM	MINIMUM inches/mm	MAXIMUM inches/mm
A		.100 / 2.540
B	.028 / 0.710	.048 / 1.220
C	.035 / 0.890	.046 / 1.170
D	.209 / 5.310	.229 / 5.840
E	.178 / 4.520	.195 / 4.950
F	.065 / 1.650	.085 / 2.160
G		.500 / 12.700
H	.012 / 0.3050	.019 / 0.4830

ORDER CODE: ASI10637

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 1.0\text{ mA}$			20			V
BV_{CBO}	$I_C = 100\text{ }\mu\text{A}$			40			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$			3.0			V
I_{CBO}	$V_{CB} = 18\text{ V}$					100	μA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 100\text{ mA}$		25		250	---
C_{OB}	$V_{CB} = 18\text{ V}$	$f = 1.0\text{ MHz}$				5.0	pF
η_C	$V_{CC} = 18\text{ V}$	$P_{OUT} = 0.7\text{ W}$	$f = 1.68\text{ GHz}$		25		%
f_t	$V_{CE} = 10\text{ V}$	$I_E = 100\text{ mA}$	$f = 200\text{ MHz}$		2500		MHz
P_{OSC}	$V_{CC} = 18\text{ V}$	$I_E = 150\text{ mA}$	$f = 1.68\text{ GHz}$		700		mW